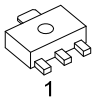
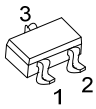
2SC3355

NPN SILICON EPITAXIAL TRANSISTOR

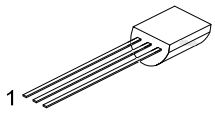
HIGH FREQUENCY LOW NOISE AMPLIFIER NPN SILICON EPITAXIAL TRANSISTOR



SOT-89



SOT-323



TO-92

■ FEATURES

* Low Noise and High Gain
* High Power Gain

■ ORDERING INFORMATION

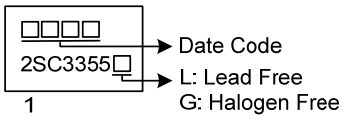
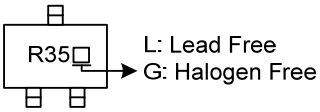
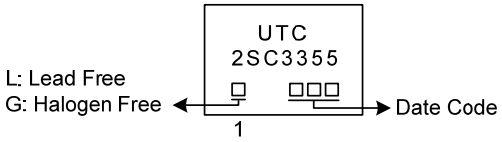
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC3355L-AB3-R	2SC3355G-AB3-R	SOT-89	B	C	E	Tape Reel
2SC3355L-AL3-R	2SC3355G-AL3-R	SOT-323	B	E	C	Tape Reel
2SC3355L-T92-B	2SC3355G-T92-B	TO-92	B	E	C	Tape Box
2SC3355L-T92-K	2SC3355G-T92-K	TO-92	B	E	C	Bulk

Note: Pin Assignment: B: Base C: Collector E: Emitter

2SC3355G-AB3-R

(1)Packing Type	(1) R: Tape Reel, B: Tape Box, K: Bulk
(2)Package Type	(2) AB3: SOT-89, AL3: SOT-323, T92: TO-92
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING

Package	MARKING
SOT-89	
SOT-323	
TO-92	

■ ABSOLUTE MAXIMUM RATING (T_A=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Collector-base voltage		V_{CBO}	20	V
Collector-emitter voltage		V_{CEO}	12	V
Emitter-base voltage		V_{EBO}	3	V
Collector current		I_C	100	mA
Power dissipation	SOT-89	P_D	500	mW
	SOT-323		200	mW
	TO-92		600	mW
Junction Temperature		T_J	+125	°C
Operating Temperature		T_{OPR}	-20 ~ +85	°C
Storage Temperature		T_{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cutoff Current	I_{CBO}	V_{CB}=10V, I_E=0			1.0	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=1V, I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=20mA	50		300	
Gain bandwidth Product	f_T	V_{CE}=10V, I_C=20mA		7		GHz
Feed-Back Capacitance	C_{re}	V_{CB}=10V, I_E=0, f=1.0MHz			1.0	pF
Noise Figure	NF	V_{CE}=10V, I_C=7mA, f=1.0GHz		1.1		dB